



**THE DATASHEET OF
HUF75333S3**



**66A, 55V, 0.016 Ohm. N-Channel UltraFET
Power MOSFETs**



These N-Channel power MOSFETs are manufactured using the innovative UltraFET® process. This advanced process technology

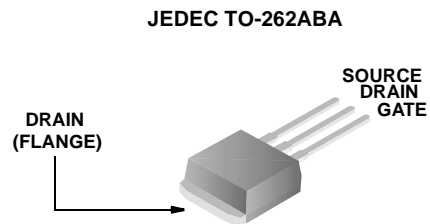
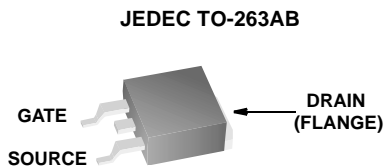
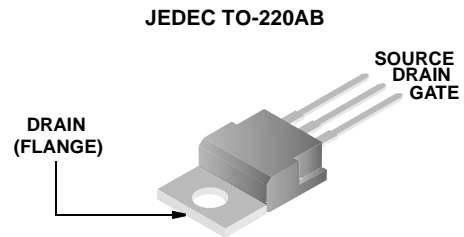
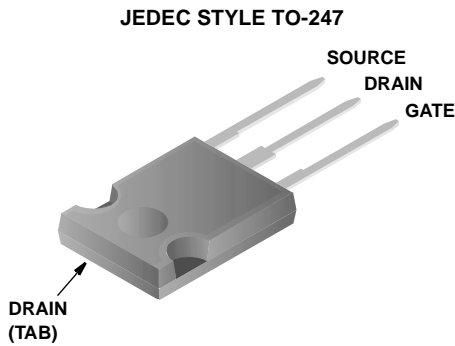
achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching convertors, motor drivers, relay drivers, low-voltage bus switches, and power management in portable and battery-operated products. .

Ordering Information

PART NUMBER	PACKAGE	BRAND
HUF75333G3	TO-247	75333G
HUF75333P3	TO-220AB	75333P
HUF75333S3S	TO-263AB	75333S
HUF75333S3	TO-262AA	75333S

NOTE: When ordering, use the entire part number. Add the suffix T to obtain the TO-263AB variant in tape and reel, e.g., HUF75333S3ST.

Packaging

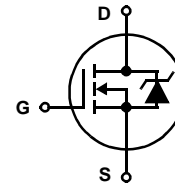


Features

- 66A, 55V
- Simulation Models
 - Temperature Compensated PSPICE® and SABER™ Models
 - SPICE and SABER Thermal Impedance Models Available on the WEB at: www.fairchildsemi.com
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Related Literature
 - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

Formerly developmental type TA75333

Symbol



Product reliability information can be found at <http://www.fairchildsemi.com/products/discrete/reliability/index.html>

For severe environments, see our Automotive HUFA series.

All Fairchild semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

HUF75333G3, HUF75333P3, HUF75333S3S, HUF75333S3

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

		UNITS
Drain to Source Voltage (Note 1)	V_{DSS}	55 V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	V_{DGR}	55 V
Gate to Source Voltage	V_{GS}	± 20 V
Drain Current		
Continuous (Figure 2)	I_D	66 A
Pulsed Drain Current	I_{DM}	Figure 4
Pulsed Avalanche Rating	E_{AS}	Figures 6, 14, 15
Power Dissipation	P_D	150 W
Derate Above 25°C		1 $\text{W}/^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 175 $^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300 $^\circ\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg}	260 $^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- $T_J = 25^\circ\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
OFF STATE SPECIFICATIONS							
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ (Figure 11)	55	-	-	V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 50\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA	
		$V_{DS} = 45\text{V}, V_{GS} = 0\text{V}, T_C = 150^\circ\text{C}$	-	-	250	μA	
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA	
ON STATE SPECIFICATIONS							
Gate to Source Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ (Figure 10)	2	-	4	V	
Drain to Source On Resistance	$r_{DS(ON)}$	$I_D = 66\text{A}, V_{GS} = 10\text{V}$ (Figure 9)	-	0.013	0.016	Ω	
THERMAL SPECIFICATIONS							
Thermal Resistance Junction to Case	$R_{\theta JC}$	(Figure 3)	-	-	1	$^\circ\text{C}/\text{W}$	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-247	-	-	30	$^\circ\text{C}/\text{W}$	
		TO-220, TO-263	-	-	62	$^\circ\text{C}/\text{W}$	
SWITCHING SPECIFICATIONS ($V_{GS} = 10\text{V}$)							
Turn-On Time	t_{ON}	$V_{DD} = 30\text{V}, I_D \equiv 66\text{A},$ $R_L = 0.455\Omega, V_{GS} = 10\text{V},$ $R_{GS} = 6.8\Omega$	-	-	100	ns	
Turn-On Delay Time	$t_{d(ON)}$		-	12	-	ns	
Rise Time	t_r		-	55	-	ns	
Turn-Off Delay Time	$t_{d(OFF)}$		-	11	-	ns	
Fall Time	t_f		-	25	-	ns	
Turn-Off Time	t_{OFF}		-	-	55	ns	
GATE CHARGE SPECIFICATIONS							
Total Gate Charge	$Q_g(TOT)$	$V_{GS} = 0\text{V}$ to 20V	$V_{DD} = 30\text{V},$ $I_D \equiv 66\text{A},$ $R_L = 0.455\Omega$ $I_g(REF) = 1.0\text{mA}$ (Figure 13)	-	70	85	nC
Gate Charge at 10V	$Q_g(10)$	$V_{GS} = 0\text{V}$ to 10V		-	40	50	nC
Threshold Gate Charge	$Q_g(TH)$	$V_{GS} = 0\text{V}$ to 2V		-	2.5	3.0	nC
Gate to Source Gate Charge	Q_{gs}			-	6.2	-	nC
Gate to Drain "Miller" Charge	Q_{gd}			-	16	-	nC

HUF75333G3, HUF75333P3, HUF75333S3S, HUF75333S3

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
CAPACITANCE SPECIFICATIONS						
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$ (Figure 12)	-	1300	-	pF
Output Capacitance	C_{OSS}		-	480	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	115	-	pF

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 66\text{A}$	-	-	1.25	V
Reverse Recovery Time	t_{rr}	$I_{SD} = 66\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	75	ns
Reverse Recovered Charge	Q_{RR}	$I_{SD} = 66\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	140	nC

Typical Performance Curves

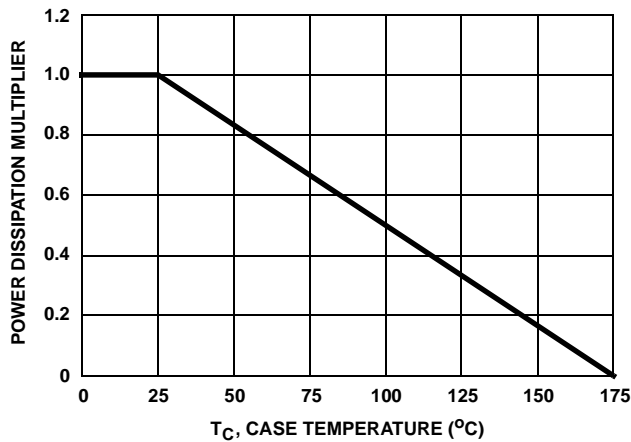


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

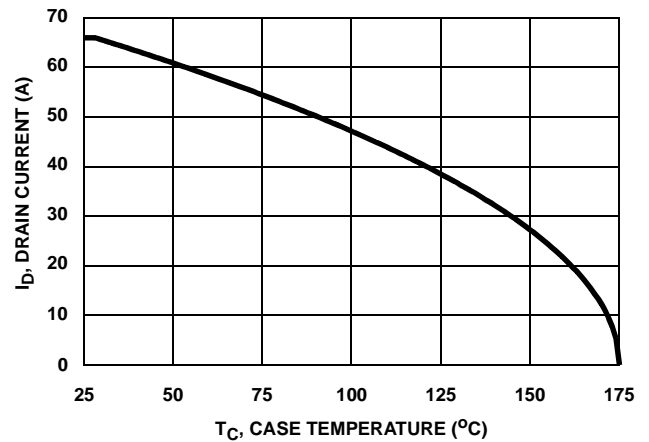


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

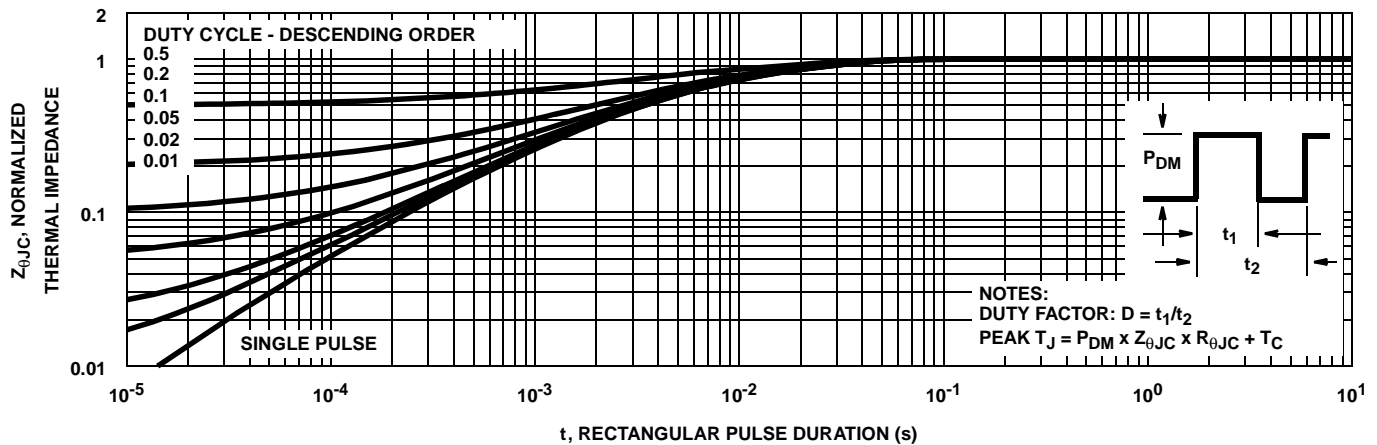


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

Typical Performance Curves (Continued)

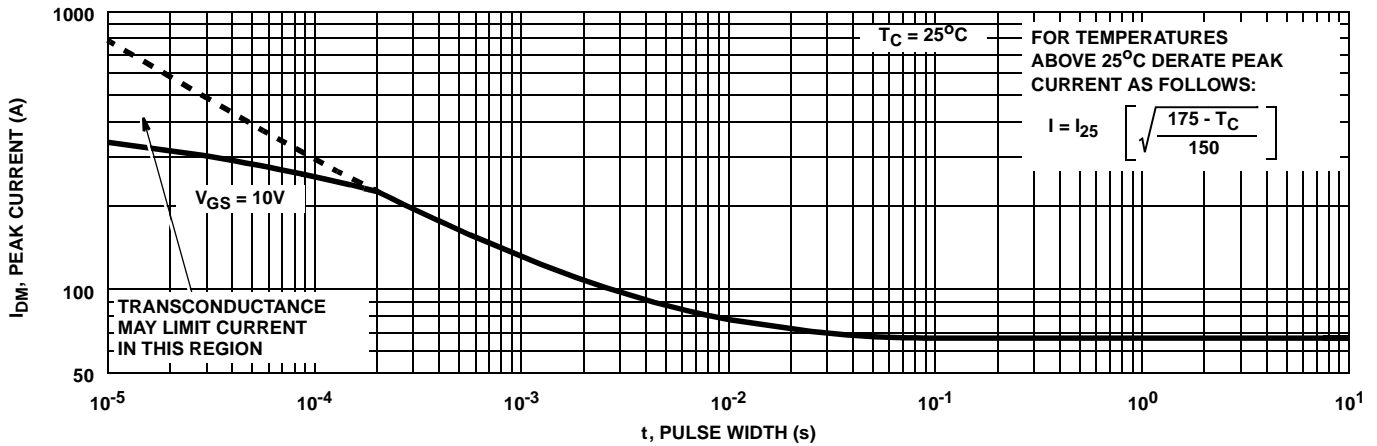


FIGURE 4. PEAK CURRENT CAPABILITY

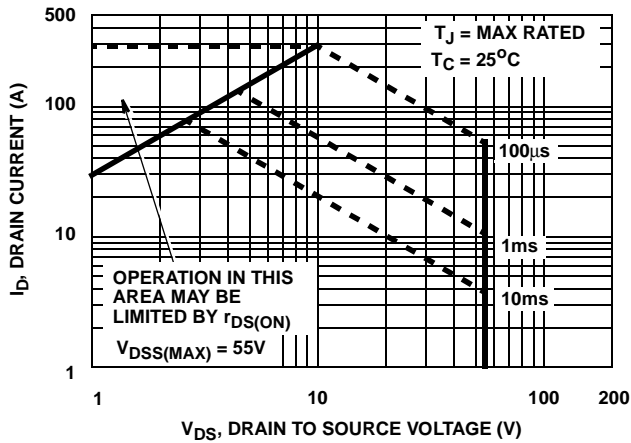
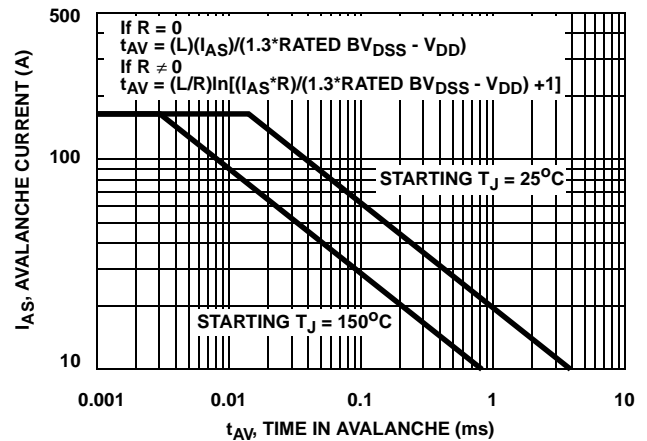


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.
FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

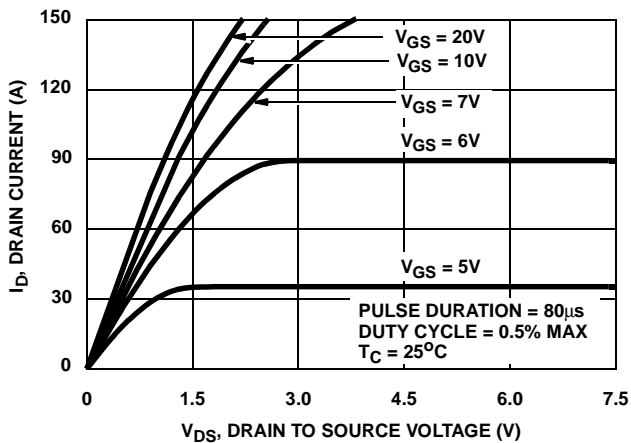


FIGURE 7. SATURATION CHARACTERISTICS

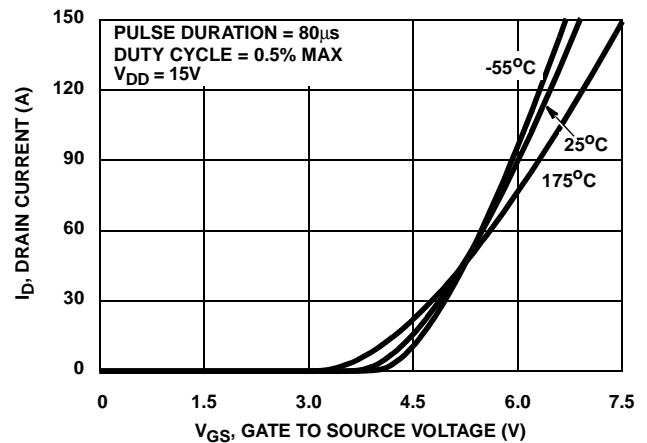


FIGURE 8. TRANSFER CHARACTERISTICS

Typical Performance Curves (Continued)

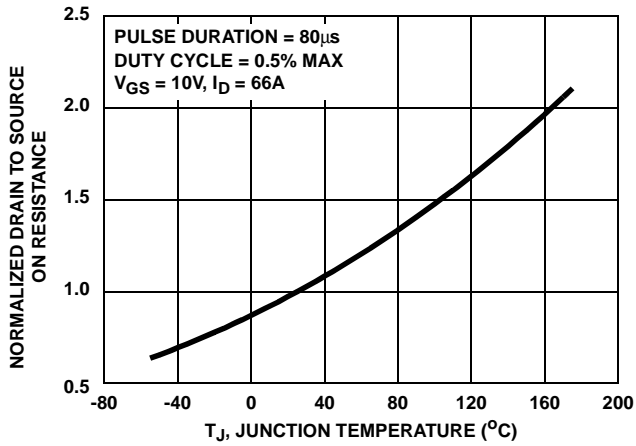


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

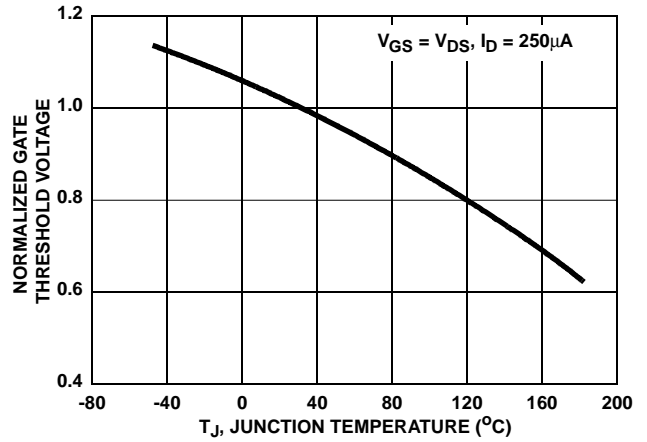


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

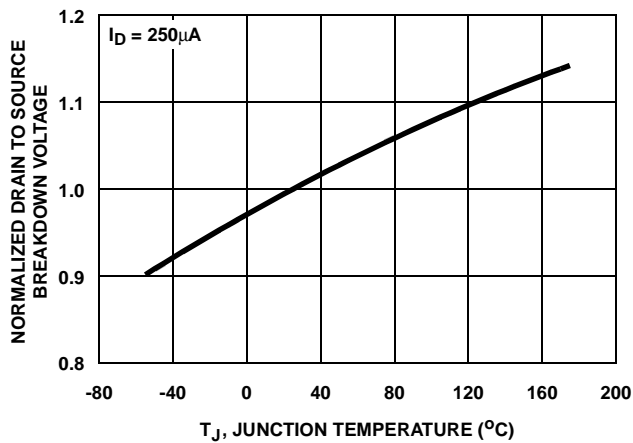


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

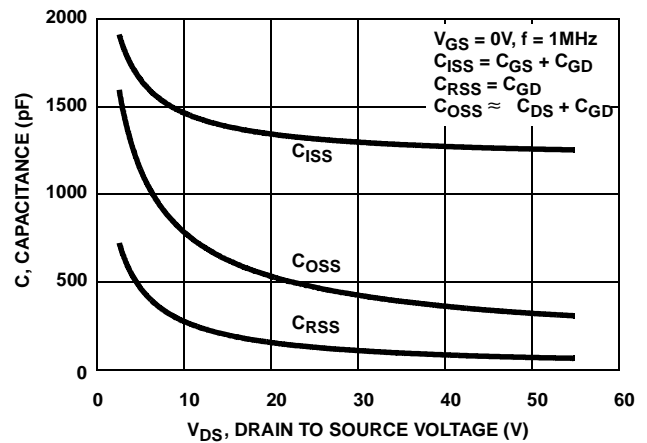
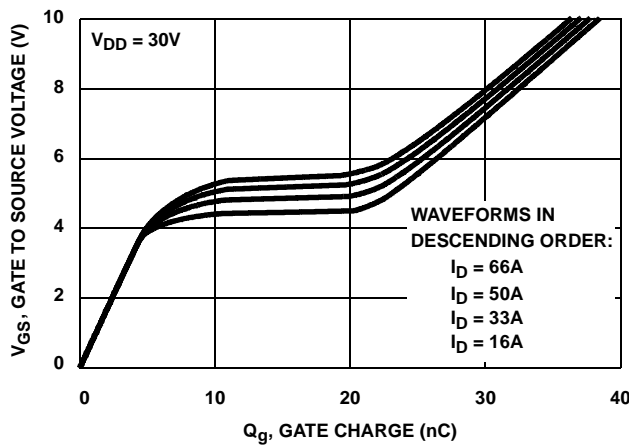


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

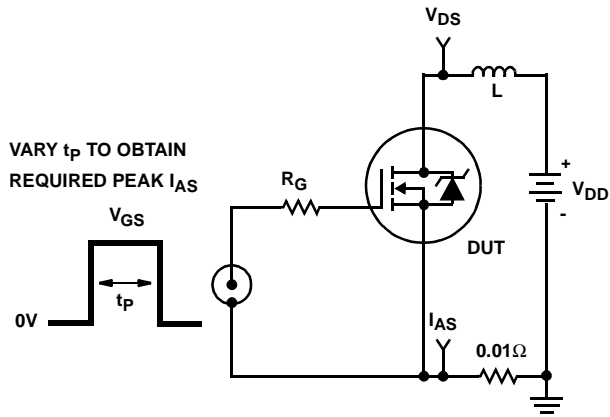


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

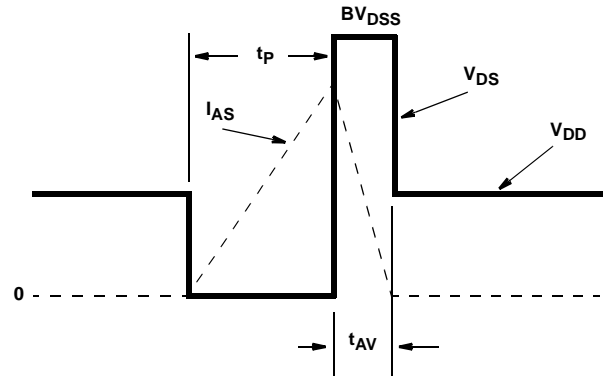


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

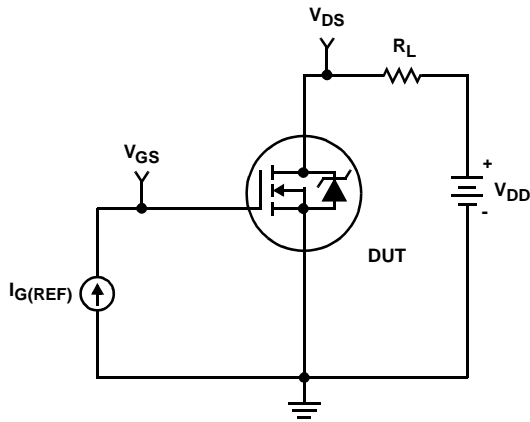


FIGURE 16. GATE CHARGE TEST CIRCUIT

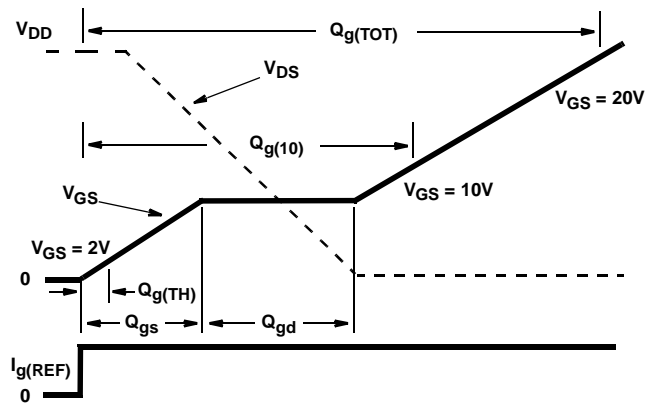


FIGURE 17. GATE CHARGE WAVEFORM

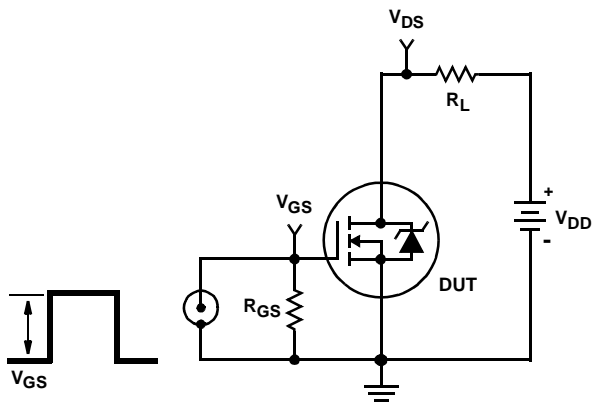


FIGURE 18. SWITCHING TIME TEST CIRCUIT

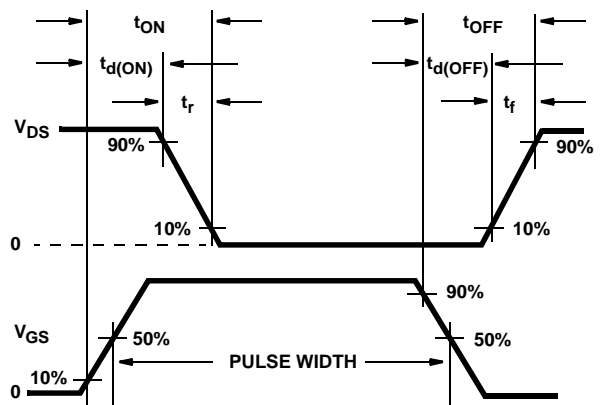


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

SABER Electrical Model

REV August 1997

template huf75333 n2, n1, n3
electrical n2, n1, n3

```
{
var i iscl
d..model dbodymod = (is = 1.3e-12, xti = 6, cjo = 1.7e-9, tt = 40e-8, n = 1, m = 0.45, vj=0.75)
d..model dbreakmod = ()
d..model dplcapmod = (cjo = 1.8e-9, is = 1e-30, n = 1, m = 0.9, vj = 1.45, fc=0.5)
m..model mmedmod = (type=_n, vto = 3.183, kp = 2, is = 1e-30, tox = 1)
m..model mstrongmod = (type=_n, vto = 3.66, kp = 51.5, is = 1e-30, tox = 1)
m..model mweakmod = (type=_n, vto = 2.703, kp = 8e-3, is = 1e-30, tox = 1)
sw_vcsp..model s1amod = (ron = 1e-5, roff = 0.1, von = -8, voff = -3)
sw_vcsp..model s1bmod = (ron = 1e-5, roff = 0.1, von = -3, voff = -8)
sw_vcsp..model s2amod = (ron = 1e-5, roff = 0.1, von = 0, voff = .5)
sw_vcsp..model s2bmod = (ron = 1e-5, roff = 0.1, von = .5, voff = 0)
```

```
c.ca n12 n8 = 1.8e-9
c.cb n15 n14 = 1.73e-9
c.cin n6 n8 = 1.19e-9
```

```
d.dbody n7 n71 = model=dbodymod
d.dbreak n72 n11 = model=dbreakmod
d.dplcap n10 n5 = model=dplcapmod
```

```
i.it n8 n17 = 1
```

```
l.ldrain n2 n5 = 1e-9
l.lgate n1 n9 = 1e-9
l.lsource n3 n7 = 1e-9
```

```
m.mmed n16 n6 n8 n8 = model=mmedmod, l = 1u, w = 1u
m.mstrong n16 n6 n8 n8 = model=mstrongmod, l = 1u, w = 1u
m.mweak n16 n21 n8 n8 = model=mweakmod, l = 1u, w = 1u
```

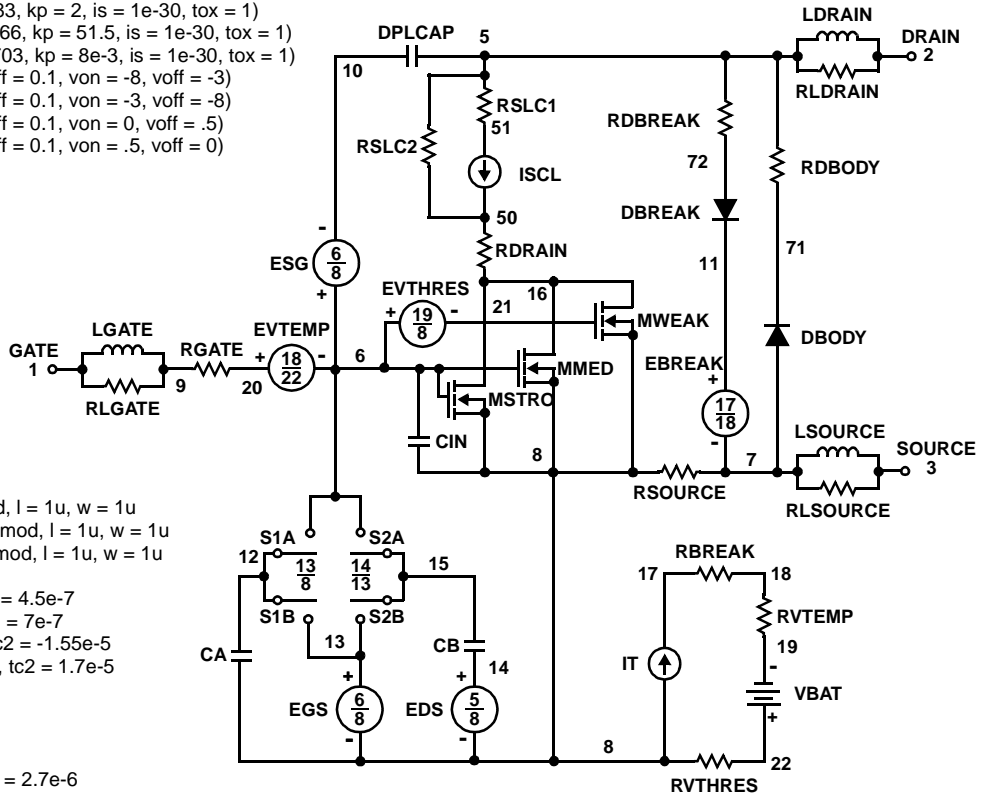
```
res.rbreak n17 n18 = 1, tc1 = 1.07e-3, tc2 = 4.5e-7
res.rbody n71 n5 = 3e-3, tc1 = 2.7e-3, tc2 = 7e-7
res.rdbreak n72 n5 = 1.1e-1, tc1 = -4e-4, tc2 = -1.55e-5
res.rdrain n50 n16 = 4.5e-3, tc1 = 1.16e-2, tc2 = 1.7e-5
res.rgate n9 n20 = 1
res.rldrain n2 n5 = 10
res.rlgate n1 n9 = 10
res.rlsource n3 n7 = 10
res.rslc1 n5 n51 = 1e-6, tc1 = 3.96e-3, tc2 = 2.7e-6
res.rslc2 n5 n50 = 1e3
res.rsource n8 n7 = 5.95e-3, tc1 = 1e-3, tc2 = 1e-5
res.rvtemp n18 n19 = 1, tc1 = -2.75e-3, tc2 = 0.5e-6
res.rvthres n22 n8 = 1, tc1 = -2.8e-3, tc2 = -1e-6
```

```
spe.ebreak n11 n7 n17 n18 = 58.85
spe.eds n14 n8 n5 n8 = 1
spe.egs n13 n8 n6 n8 = 1
spe.esg n6 n10 n6 n8 = 1
spe.evtemp n20 n6 n18 n22 = 1
spe.evthres n6 n21 n19 n8 = 1
```

```
sw_vcsp.s1a n6 n12 n13 n8 = model=s1amod
sw_vcsp.s1b n13 n12 n13 n8 = model=s1bmod
sw_vcsp.s2a n6 n15 n14 n13 = model=s2amod
sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod
```

```
v.vbat n22 n19 = dc = 1
```

```
equations {
i (n51->n50) += iscl
iscl: v(n51,n50) = (((v(n5,n51))/(1e-9+abs(v(n5,n51))))*(abs(v(n5,n51))*1e6/180)** 4))
}
}
```



SPICE Thermal Model

REV January 1999

HUF75333

CTHERM1 th 6 4.9e-4
 CHERM2 6 5 4.5e-3
 CHERM3 5 4 6.0e-3
 CHERM4 4 3 8.5e-3
 CHERM5 3 2 1.0e-2
 CHERM6 2 tl 5.0e-2

R THERM1 th 6 6.0e-4
 R THERM2 6 5 6.8e-3
 R THERM3 5 4 3.3e-2
 R THERM4 4 3 9.7e-2
 R THERM5 3 2 3.3e-1
 R THERM6 2 tl 3.6e-1

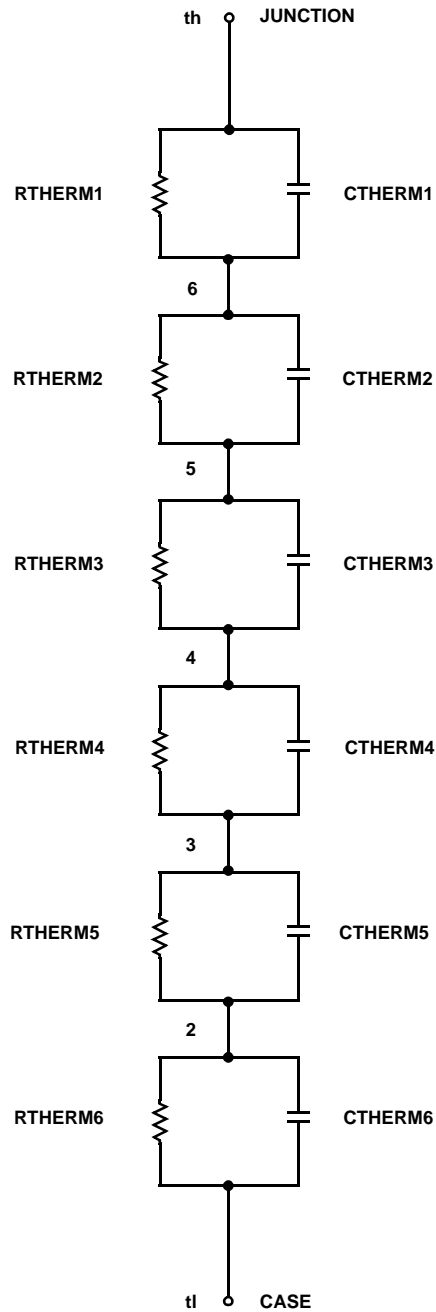
SABER Thermal Model

SABER thermal model HUF75333

template thermal_model th tl
 thermal_c th, tl

```
{
ctherm.ctherm1 th 6 = 4.9e-4
ctherm.ctherm2 6 5 = 4.5e-3
ctherm.ctherm3 5 4 = 6.0e-3
ctherm.ctherm4 4 3 = 8.5e-3
ctherm.ctherm5 3 2 = 1.0e-2
ctherm.ctherm6 2 tl = 5.0e-2
```

```
rtherm.rtherm1 th 6 = 6.0e-4
rtherm.rtherm2 6 5 = 6.8e-3
rtherm.rtherm3 5 4 = 3.3e-2
rtherm.rtherm4 4 3 = 9.7e-2
rtherm.rtherm5 3 2 = 3.3e-1
rtherm.rtherm6 2 tl = 3.6e-1
}
```



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Bottomless™	FAST®	LittleFET™	Power247™	SuperSOT™-3
CoolFET™	FASTr™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic®
E ² CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	µC™	OCX™	RapidConfigure™	UHC™
Across the board. Around the world.™		OCXPro™	RapidConnect™	UltraFET®
The Power Franchise™		OPTOLOGIC®	SILENT SWITCHER®	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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